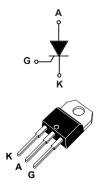


High temperature 50 A SCRs



TO-220AB insulated

Features

- High junction temperature: T_j = 150 °C
- High noise immunity dV/dt = 500V/µs up to 150 °C
- Gate triggering current I_{GT} = 15 mA
- Peak off-state voltage V_{DRM}/V_{RRM} = 600 V
- High turn-on current rise dI/dt = 100 A/μs
- ECOPACK®2 compliant
- Insulated package TO-220AB:
 - Insulated voltage: 2500 V_{RMS}
 - Complies with UL 1557 (File ref : E81734)

Applications

- · Motorbike voltage regulator circuits
- · Inrush current limiting circuits
- · Motor control circuits and starters
- Solid state relays
- Overvoltage crowbar protection

Description

The TN5015H-6I offers high thermal performance operation up to 50 A thanks to its junction temperature T_j up to 150 °C. Its fully tab insulated (thanks to ceramic inside) TO-220AB package allows a back to back configuration.

Its trade-off noise immunity (dV/dt = 500 V/ μ s) versus its gate triggering current (I_{GT} = 15 mA) and its turn-on current rise (dI/dt = 100 A/ μ s) allow to design robust and compact control circuit for voltage regulator in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen appliances, inrush current limiting circuits.

Product status	
TN5015H-6I	

Product summary		
Order code	TN5015H-6I	
Package	TO-220AB Ins.	
V_{DRM}/V_{RRM}	600 V	
I _{GT}	15 mA	



1 Characteristics

Table 1. Absolute maximum ratings (limiting values), $T_j = 25$ °C unless otherwise specified

Symbol	Pa	rameter		Value	Unit
I _{T(RMS)}	RMS on-state current (180 ° conduction angle)		T _c = 75 °C	50	Α
			T _c = 81 °C	30	
I _{T(AV)}	Average on-state current (180 ° condu	iction angle)	T _c = 97 °C	25	Α
		20			
	Non repetitive curse neek on state ou	cront (T. initial = 25 °C)	$t_p = 8.3 \text{ ms}$	493	
I _{TSM}	Non repetitive surge peak on-state cur	rient (1 _j initial – 25 °C)	t _p = 10 ms	450	Α
I _{PP} ⁽¹⁾	R_{G-A} = 3 k Ω , 8/20 us current shape, 10	0 pulses	'	1500	Α
l ² t	I ² t value for fusing		t _p = 10 ms	1012	A ² s
dl/dt	I _G = 2 x I _{GT} , tr ≤ 100 ns		f = 60 Hz	100	A/µs
di/dt	Critical rate of rise of on-state current		1 - 00 HZ	100	Ανμδ
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage T_j = 150 °C		600	V	
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state vol	tage	t _p = 10 ms	V _{DRM} /V _{RRM} + 100	V
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation		T _j = 150 °C	1	W
V_{RGM}	Maximum peak reverse gate voltage		'	5	V
T _{stg}	Storage junction temperature range	-40 to +150	°C		
T _j	Maximum operating junction temperate	-40 to +150	°C		
T _I	Maximum lead temperature soldering during 10 s			260	°C
V _{ins}	Insulation RMS voltage, 1 minute			2500	V

^{1.} According to IEC61000-4-5 standard (See Section 2)

Table 2. Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test conditions				
I _{GT}	$V_D = 12 \text{ V. } R_1 = 33 \Omega$	/ 40 V P 20 0			
V _{GT}	VD - 12 V, NL - 33 12		Max.	1.3	V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$	T _j = 150 °C	Min.	0.15	V
I _H	I _T = 500 mA, gate open		Max.	60	mA
IL	$I_G = 1.2 \times I_{GT}$		Max.	80	mA
dV/dt	V _D = 402 V, gate open	T _j = 150 °C	Min.	500	V/µs
t _{gt}	I_{TM} = 100 A, V_D = 402 V, I_G = 30 mA, (d I_G /dt) max = 0.2 A/ μ s	*	Тур.	1.9	μs
t _q	I_{TM} = 100 A, V_D = 402 V, (dI_T/dt) max = 30 A/ μ s, V_R = 25 V, dV_D/dt = 50 V/ μ s	Тур.	85	μs	

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Table 3. Static characteristics

Symbol	Test conditions			Value	Unit
V _{TM}	I_{TM} = 100 A, t_p = 380 μ s	T _j = 25 °C	Max.	1.65	V
V _{TO}	Threshold voltage	T _j = 150 °C	Max.	0.85	V
R _D	Dynamic resistance	T _j = 150 °C	Max.	9	mΩ
I _{DRM} , I _{RRM}	$V_D = V_{DRM} = V_{RRM}$	T _j = 25 °C	May	10	μA
	VD - VDRM - VRRM	T _j = 150 °C	Max.	6	mA

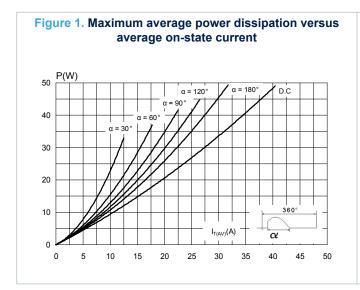
Table 4. Thermal parameters

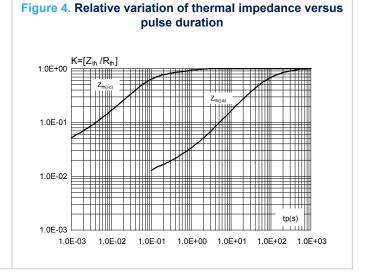
Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case (DC)	Max.	1.5	°C/W
R _{th(j-a)}	Junction to ambient (DC)	Тур.	60	C/VV

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1.1 Characteristics curves





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Figure 5. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

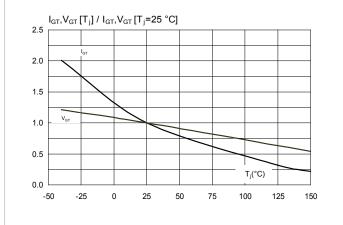


Figure 6. Relative variation of holding and latching current versus junction temperature (typical values)

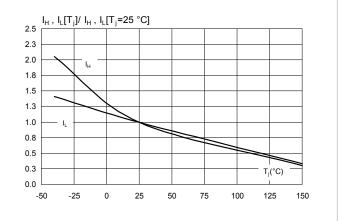


Figure 7. Relative variation of static dV/dt immunity versus junction temperature (typical values)

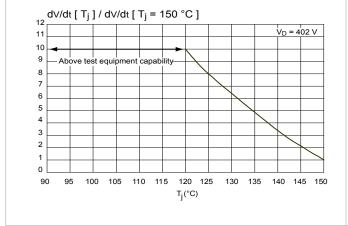


Figure 8. Surge peak on-state current versus number of cycles

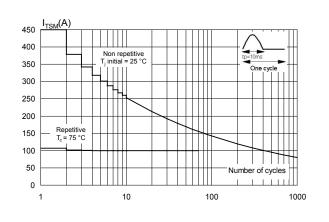


Figure 9. Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10 \text{ ms}$

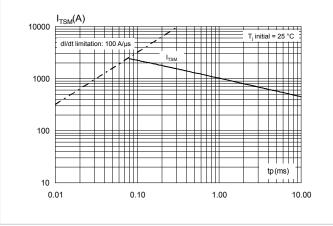
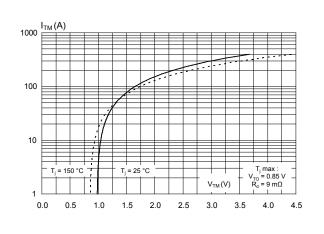


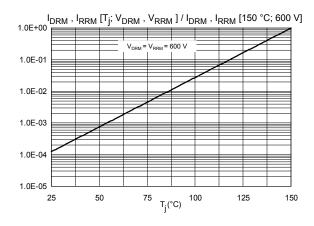
Figure 10. On-state characteristics (maximum values)



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Figure 11. Relative variation of leakage current versus junction temperature



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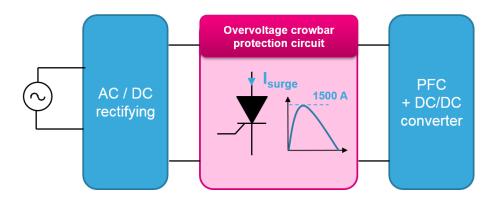


2 Application information

2.1 Overvoltage crowbar protection

An application featuring the strong current robustness of TN5015H-6I is the overvoltage crowbar protection, implemented in AC/DC switch mode power supply. An application global schematic is shown Figure 12. Global schematic of a crowbar overvoltage protection application.

Figure 12. Global schematic of a crowbar overvoltage protection application



In case of overvoltage on line power terminals (example: lightning event), the voltage is rising quickly across the DC/DC module and can reach voltages limitations of devices, leading to possible application failure. The overvoltage crowbar protection answers to this issue by placing the SCR in parallel of the rectifier bridge output, and limiting the induced surge current during electrical over-stress.

The protection principle is to trig the TN5015H-6I when the overvoltage reaches the maximum authorized voltage. At TN5015H-6I turn-on, the electrical overvoltage stress becomes an overcurrent stress, flowing through the TN5015H-6I. No more voltage stress is applied across the down stream converter and the TN5015H-6I absorbs the overcurrent, making the application safe.

Additionally, the AC/DC SMPS efficiency and stand-by losses are not impacted by the protection thanks to the very low leakage current of the TN5015H-6I.

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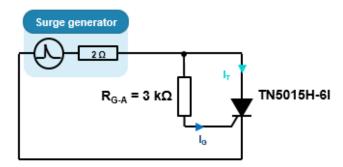
2.2 Peak pulse current robustness

The TN5015H-6I overcurrent capability is guaranteed through a specific parameter called peak pulse current: I_{PP}. This is the maximum current robustness of TN5015H-6I for an 8/20 us current waveform, as described in the IEC61000-4-5 standard.

The Figure 13. I_{PP} 8/20 μ s test circuit illustrates the test circuit for the I_{PP} parameter. The overstress is applied 10 times (according to the same standard) with a 1.2/50 μ s overvoltage and 8/20 μ s overcurrent stress generator.

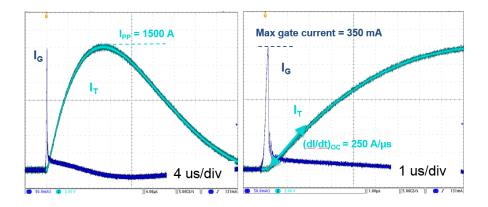
Figure 13. I_{PP} 8/20 µs test circuit





The Figure 14. I_{PP} 8/20 μ s test waveform (left part) is the 8/20 μ s waveform of current through the TN5015H-6I under test. The maximum gate current in this case is 350 mA (zoom at SCR triggering in the right part) and the maximum non-repetitive rate of current (dI/dt)_{OC} is 250 A/ μ s.

Figure 14. I_{PP} 8/20 µs test waveform



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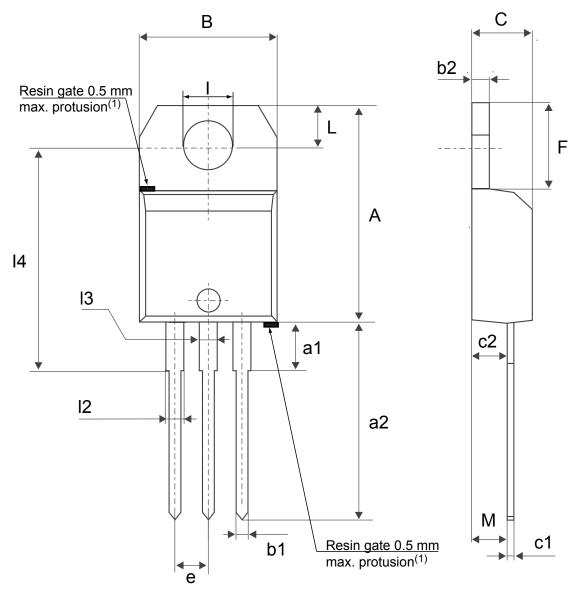
3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

3.1 TO-220AB insulated package information

- Molding compound resin is halogen-free and meets UL standard level V0
- · Lead-free package leads finishing
- ECOPACK®2 compliant

Figure 15. TO-220AB insulated package outline



(1) Resin gate position accepted in one of the two positions or in the symmetrical opposites.

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Table 5. TO-220AB insulated package mechanical data

			Di	mensions		
Ref.		Millimeters			Inches ⁽¹⁾	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
В	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
С	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
е	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
1	3.73		3.88	0.1469		0.1528
L	2.65		2.95	0.1043		0.1161
12	1.14		1.70	0.0449		0.0669
13	1.14		1.70	0.0449		0.0669
14	15.80	16.40	16.80	0.6220	0.6457	0.6614
М		2.6			0.1024	

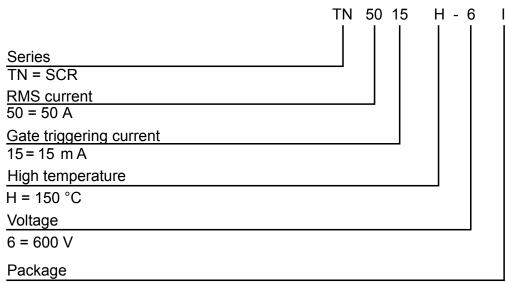
^{1.} Inch dimensions are for reference only.

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4 Ordering information

Figure 16. Ordering information scheme



I = TO-220AB insulated

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN5015H-6I	TN5015H6I	TO-220AB ins.	2.3 g	50	Tube

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Revision history

Table 7. Document revision history

Date	Revision	Changes
02-Jun-2017	1	Initial release.
01-Dec-2017	2	Inserted Section 6: "Application information"and updated Table 2: "Absolute maximum ratings (limiting values), Tj = 25 °C unless otherwise specified"
08-Oct-2018	3	Updated Section Cover image.

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